Supporting Information

Improved Resistive Switching Characteristics of multi-stacked HfO₂/Al₂O₃/HfO₂ RRAM structure for neuromorphic and synaptic applications: Experimental and Computational study

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Figure S1. The geometry optimized Energy vs. Volume plots using Birch Murnaghan equation of states.
Figure S2. The calculated Density of States (DOS) using VASP simulation code.